

**SANYO**

No. 5025

**STK730-020****Self-Excitation Type Semi-Regulated  
Switching Regulator (145W Output)****Overview**

The STK730-020 incorporates on-chip all the power switching, amplifier, error detection and overcurrent protection circuits required in a self-excitation type semi-regulated off-line switching regulator. As a result, it can be used in the design of switching power supplies with minimal number of external components. Furthermore, the adoption of MOSFET power switching elements supports a higher oscillator frequency than that possible with bipolar transistors. This allows smaller pulse transformers and capacitors to be used, making it possible to construct miniature power supply systems.

**Applications**

- CRT/CTV power supplies
- Office automation equipment power supplies

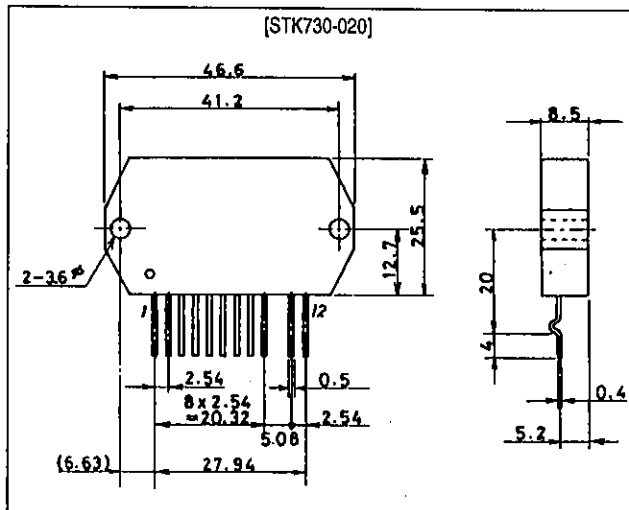
**Features**

- Power MOSFET devices
- Ideal for semi-regulated control switching supplies
- Error detection circuit on-chip ( $40.5 \pm 0.5V$  set reference voltage)
- Overcurrent protection circuit on-chip
- Pin compatible with all other devices in the same series of devices with 110 to 280W power ratings
- Higher oscillator frequency allows the use of smaller pulse transformers
- IMST substrate acts as an electromagnetic shield, making low-noise designs possible

**Package Dimensions**

unit: mm

4121



## STK730-020

### Specifications

**Maximum Ratings** at  $T_a = 25^\circ\text{C}$ ,  $T_c = 25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Operating substrate temperature	$T_c \text{ max}$	Recommended value is $105^\circ\text{C}$ .	115	$^\circ\text{C}$
AC input voltage	$V_{AC}$	Specified test circuit	140	Vrms
Operating temperature	$T_{opr}$		-10 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-30 to +115	$^\circ\text{C}$
Maximum output power	$W_o \text{ max}$	Specified test circuit, $V_O = 135\text{V}$	150	W
<b>[TR1]</b>				
Drain current	$I_D$	Refer to ASO characteristics for overcurrent condition.	8	A
Pulse drain current	$I_{D(pulse)}$		30	A
Drain reverse current	$I_{DR}$		8	A
Gate-source voltage	$V_{GSS}$		$\pm 30$	V
Allowable power dissipation	$P_D$		89.3	W
Chip junction temperature	$T_J \text{ max}$		150	$^\circ\text{C}$
Thermal resistance	$\theta_{j-c}$		1.4	$^\circ\text{C/W}$
<b>[ZD1]</b>				
Allowable power dissipation	$P_{ZD1}$		500	mW
Chip junction temperature	$T_{J(ZD1)} \text{ max}$		125	$^\circ\text{C}$
Thermal resistance	$\theta_{j-c(ZD1)}$		0.2	$^\circ\text{C/mW}$

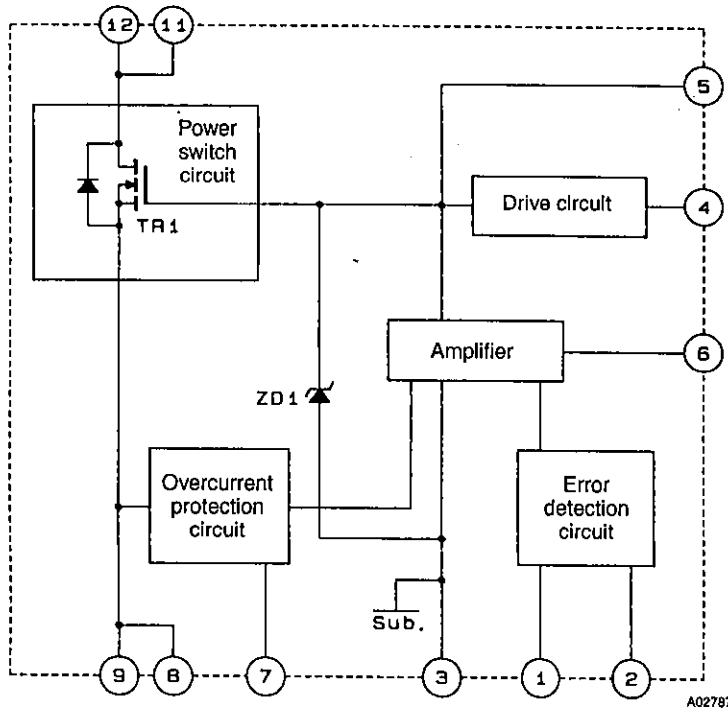
**Recommended Operating Conditions** at  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Pin 4 input voltage	$V_4$		$\pm 8$ to $\pm 24$	V
Oscillator frequency	$f_{osc}$		20 to 120	kHz

**Operating Characteristics** at  $T_a = 25^\circ\text{C}$ ,  $T_c = 25^\circ\text{C}$  unless otherwise specified, specified test circuit

Parameter	Symbol	Conditions	min	typ	max	Unit
Output voltage setting		$I_{in} = 8\text{mA}$	40.0	40.5	41.0	V
Output voltage temperature coefficient		$T_c = 0$ to $105^\circ\text{C}$ , $I_{in} = 8\text{mA}$	-	7	-	$\text{mV}/^\circ\text{C}$
<b>[TR1]</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{mA}$ , $V_{GS} = 0\text{V}$	500	-	-	V
Gate-source cutoff voltage	$V_{GS(off)}$	$I_D = 1\text{mA}$ , $V_{DS} = 10\text{V}$	2.0	-	3.0	V
ON resistance	$R_{DS(on)}$	$I_D = 4.0\text{A}$ , $V_{GS} = 10\text{V}$	-	0.8	1.1	$\Omega$
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	1200	-	pF
<b>[ZD1]</b>						
Zener voltage	$V_Z$	$I_Z = 5\text{mA}$	23.7	-	26.3	V

**Block Diagram**



**Pin Functions**

Pin No.	Function
1	$V_{ref}$ (40.5V typ) input
2	Error detection level
3	Ground
4	Drive voltage input
5	TR1 gate
6	Amplifier circuit control
7	OCP setting level input
8	TR1 source
9	
11	TR1 drain
12	

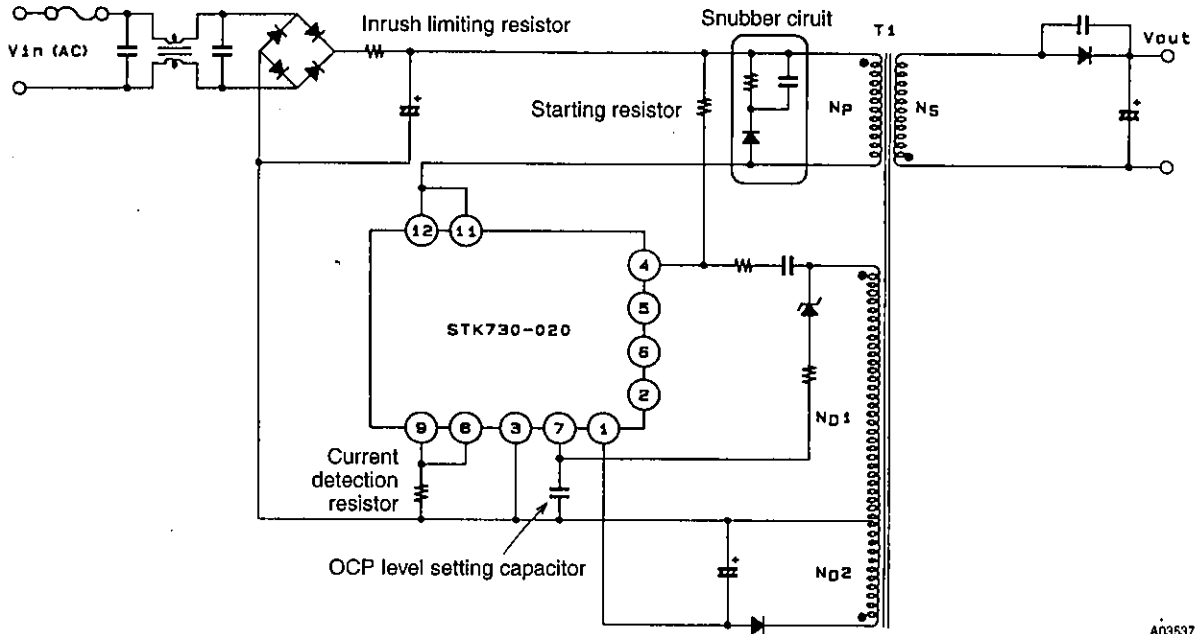
The back surface of the IC is not an insulator, and is effectively at pin 3 potential.

**Series Organization**

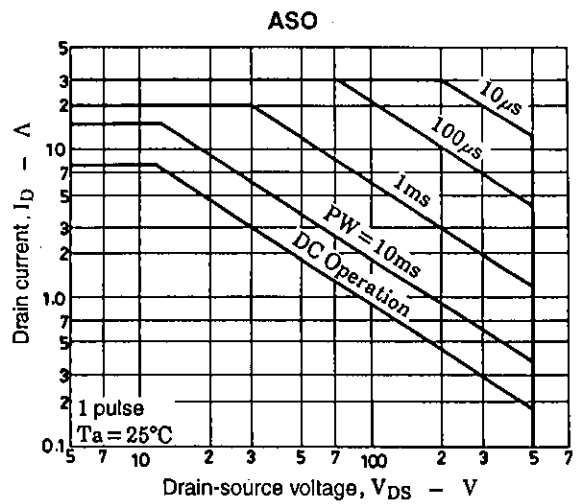
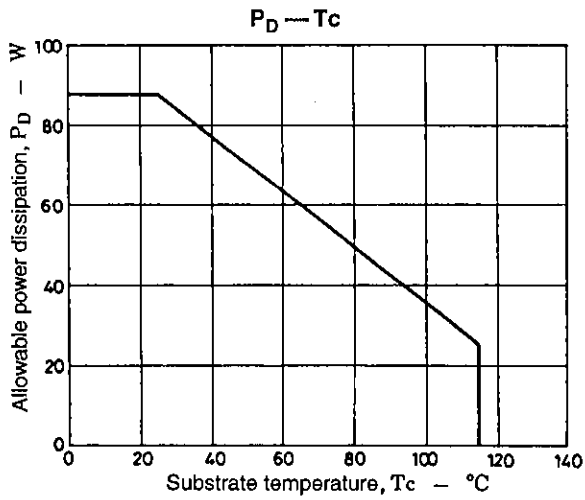
These devices form a series with varying output power ratings.

Type No.	Maximum ratings					Operating characteristics		
	$V_{pss}$ [V]	$T_{stg}$ [°C]	$T_c \text{ max}$ [°C]	$T_j \text{ max}$ [°C]	$I_o$ [A]	Input voltage [V]	Output power [W]	ON resistance [ $\Omega$ ]
STK730-010	500	-30 to +115	+115	+150	6.0	85 to 132	110	1.4
STK730-020					8.0		145	0.8
STK730-030					10.0		180	0.7
STK730-040					12.0		210	0.55
STK730-050					15.0		280	0.3
STK730-060	900				3.0	170 to 264	110	5.0
STK730-070					5.0		180	3.0
STK730-080					6.0		210	2.0
STK730-090					8.0		280	1.2

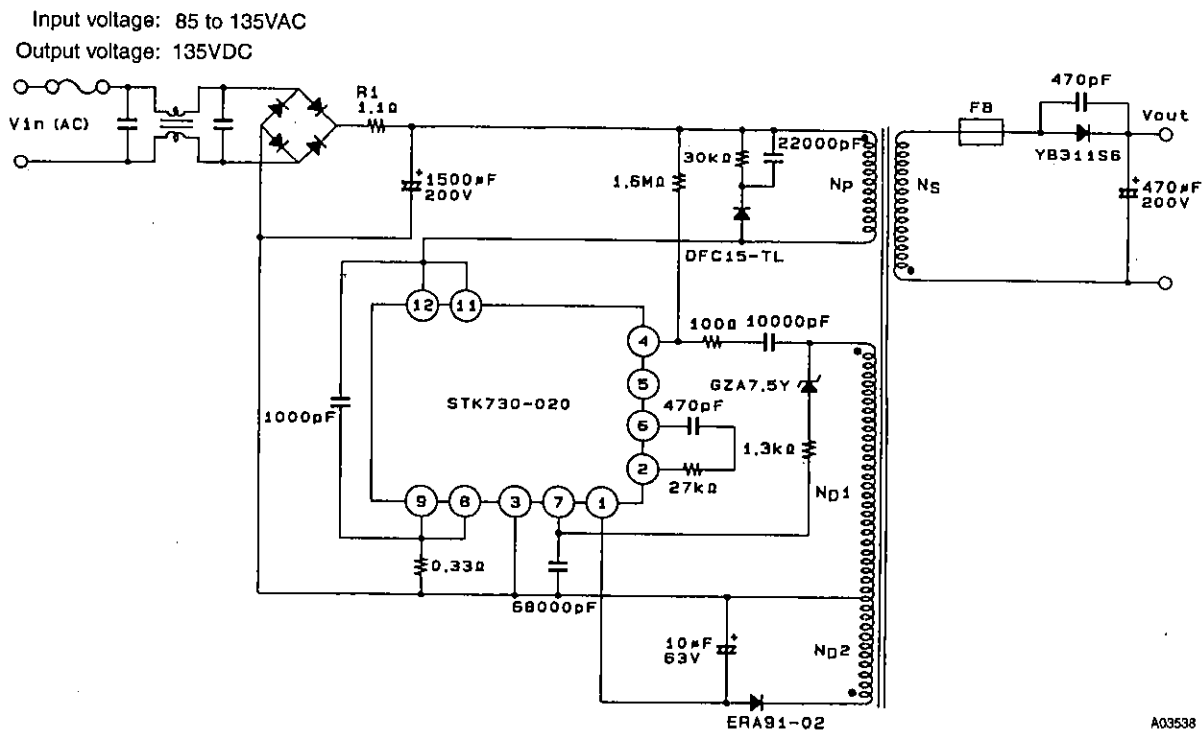
Circuit Function Diagram



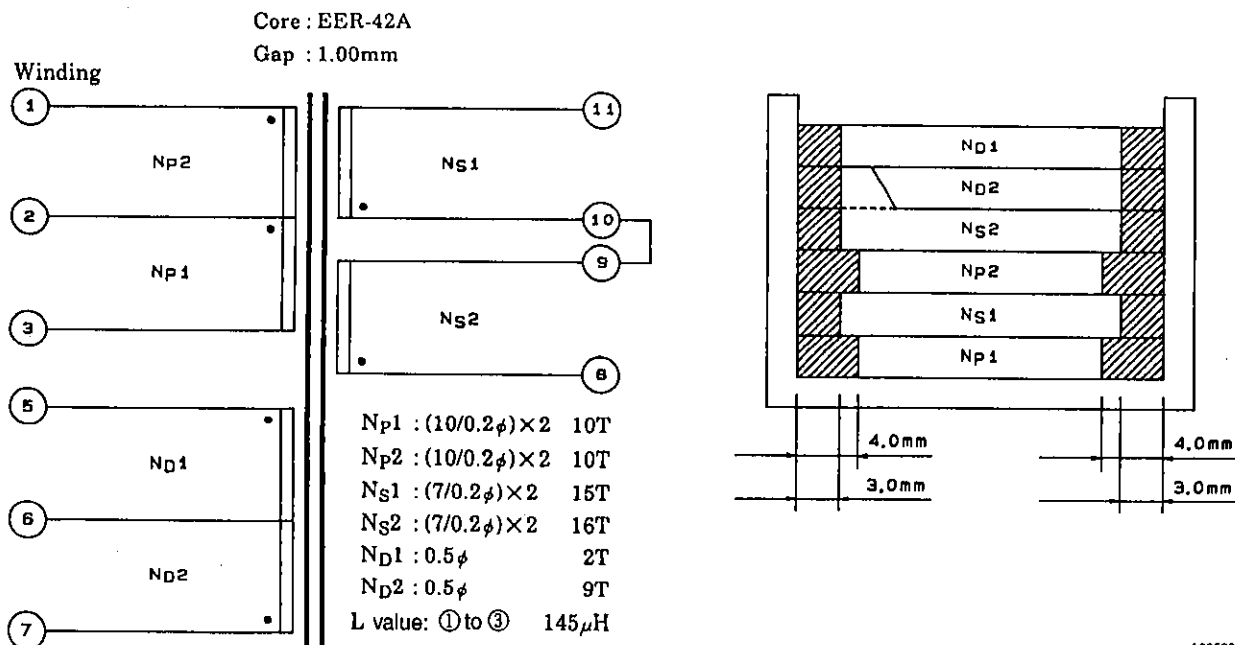
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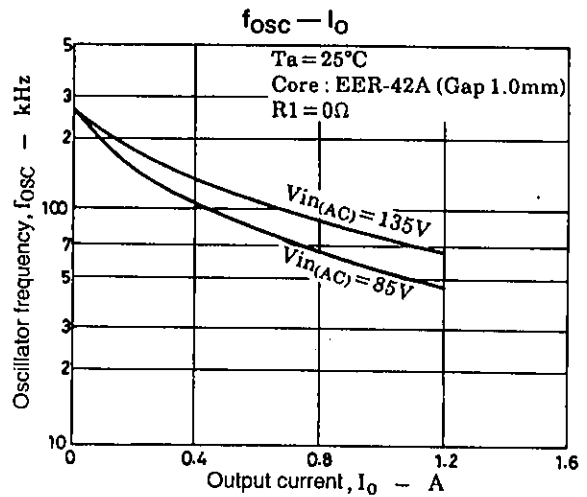
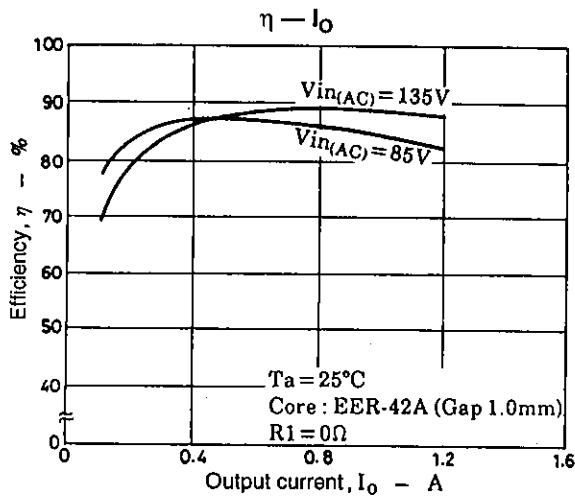
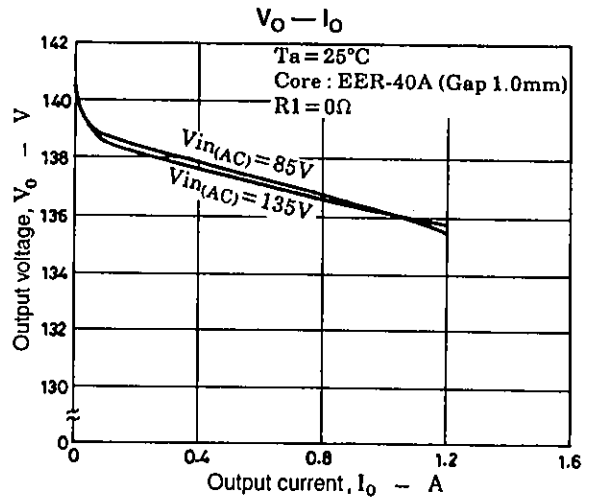
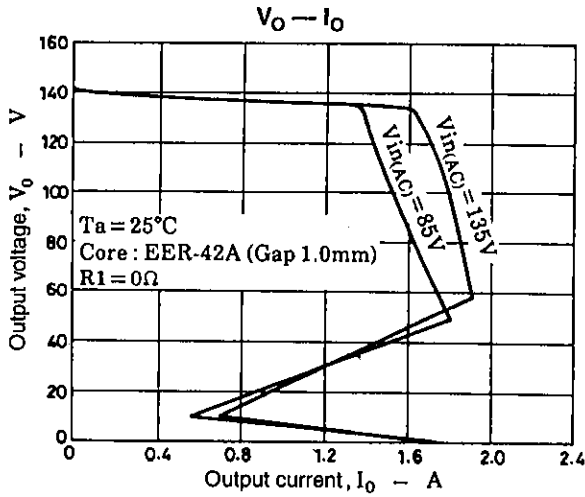


### Sample Application Circuit



### Pulse Transformer Specifications





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